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PATENT NUMBER

U.S. UTILITY Patent Application

OLP.E

PATENT DATE

SCANNED

TITLE **APPLICANTS**

Bin Yu

[illegible]

Method of fabricating a semiconductor device by atomic layer deposition (ALD) and a substrate for the same

PTO-2040
12/99[illegible]

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	_____ (Assistant Examiner) _____ (Date)			NOTICE OF ALLOWANCE MAILED _____	
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